



12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20241119009.2

**Qualification of RFAB & MIHO8 Fabs using qualified Process Technologies, Die Revision, Datasheet, and new Assembly/Test site (MLA) & BOM options for select devices
Change Notification / Sample Request**

Date: November 20, 2024

To: MOUSER PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments (TI). The details of this change are on the following pages, and are in alignment with our standard product change notification (PCN) [process](#).

TI requires acknowledgement of receipt of this notification within 30 days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 30 days of this notification, given that samples are not built ahead of the change.

The Proposed First Ship date in this PCN letter is the earliest possible date that customers could receive the changed material. It is our commitment that the changed device will not ship before that date. If samples are requested within the 30 day sample request window, customers will still have 30-days to complete their evaluation regardless of the proposed 1st ship date.

Changes outlined in this notification underscore our commitment to product longevity and supply continuity, as well as our continued efforts to transition to newer, more efficient manufacturing processes and technologies. Specifically, this particular notification is related to TI's multiyear transition plan for our two remaining 150-millimeter production lines (DFAB in Dallas, Texas, and SFAB in Sherman, Texas). SFAB closure activities are expected to begin by the end of 2025. DFAB will remain open with a smaller set of 200mm technologies and GaN.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the Change Management team. For sample requests or sample related questions, contact your local Field Sales Representative. As always, we thank you for your continued business.

Change Management Team
SC Business Services


20241119009.2
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
ISO7220AQDRQ1	ISO7220AQDRQ1
ISO7231CQDWRQ1	ISO7231CQDWRQ1
ISO7240CFQDWRQ1	ISO7240CFQDWRQ1
ISO7221AQDRQ1	ISO7221AQDRQ1
ISO7241CQDWRQ1	ISO7241CQDWRQ1
ISO7242CQDWRQ1	NULL
ISO7221CQDRQ1	ISO7221CQDRQ1

Technical details of this Product Change follow on the next page(s).

PCN Number:	20241119009.2		PCN Date:	November 20, 2024																			
Title:	Qualification of RFAB & MIHO8 Fabs using qualified Process Technologies, Die Revision, Datasheet, and new Assembly/Test site (MLA) & BOM options for select devices																						
Customer Contact:	Change Management Team		Dept:	Quality Services																			
Proposed 1st Ship Date:	May 19, 2025		Sample requests accepted until:	December 20, 2024*																			
*Sample requests received after December 20, 2024 will not be supported.																							
Change Type:																							
<input checked="" type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Material																		
<input checked="" type="checkbox"/>	Assembly Process	<input checked="" type="checkbox"/>	Data Sheet	<input checked="" type="checkbox"/>	Wafer Bump Process																		
<input checked="" type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input checked="" type="checkbox"/>	Wafer Fab Site																		
<input type="checkbox"/>	Mechanical Specification	<input checked="" type="checkbox"/>	Test Site	<input checked="" type="checkbox"/>	Wafer Fab Material																		
<input checked="" type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input checked="" type="checkbox"/>	Wafer Fab Process																		
PCN Details																							
Description of Change:																							
Texas Instruments is pleased to announce the addition of RFAB & MIHO8 Fabs using the LBC9 & ISOSAX qualified process technologies, Assembly/Test site (MLA) and BOM options for the devices listed below.																							
<table border="1"> <thead> <tr> <th colspan="3">Current Fab Site</th> <th colspan="3">Additional Fab Site</th> </tr> <tr> <th>Current Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Additional Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>DL-LIN (2 die)</td> <td>LBC4</td> <td>150 mm</td> <td>RFAB (2 die) MIHO8 (1 die)</td> <td>LBC9 ISOSAX</td> <td>300 mm 200 mm</td> </tr> </tbody> </table>			Current Fab Site			Additional Fab Site			Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	DL-LIN (2 die)	LBC4	150 mm	RFAB (2 die) MIHO8 (1 die)	LBC9 ISOSAX	300 mm 200 mm			
Current Fab Site			Additional Fab Site																				
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter																		
DL-LIN (2 die)	LBC4	150 mm	RFAB (2 die) MIHO8 (1 die)	LBC9 ISOSAX	300 mm 200 mm																		
The die were also changed as a result of the process change.																							
		Current			New																		
Probe site		No Probe			CD-PR																		
Construction differences are as follows:																							
Group 1 device																							
	TAI		MLA																				
Wire diam/type	1.3mil Au		0.8mil Cu																				
Mold compound	4209640		4221499																				
Group 2 device																							
	TAI		MLA																				
Wire diam/type	0.96mil Au		0.8mil Cu																				
Mold compound	4209640		4211880																				
The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history. The links to the revised datasheets are available in the table below.																							
<div style="display: flex; justify-content: space-between; align-items: center;">  <div> ISO7240CF-Q1, ISO7241C-Q1, ISO7242C-Q1 <small>SLISE40B – SEPTEMBER 2010 – REVISED NOVEMBER 2024</small> </div> </div>																							

Changes from Revision A (September 2011) to Revision B (November 2024)	Page
• Updated reference from capacitive isolation to isolation barrier throughout the document.....	1
• Updated VDE V 0884-11 to DIN VDE 0884-17 throughout the document.....	1
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Updated Thermal Characteristics, Safety Limiting Values, and Thermal Derating Curves to provide more accurate system-level thermal calculations.....	5
• Updated electrical and switching characteristics to match device performance.....	7
• Added the <i>Detailed Description</i> , <i>Overview</i> , <i>Feature Description</i> , <i>Functional Block Diagram</i> , and <i>Device Functional Modes</i> sections.....	19
• Added the <i>Typical Application</i> , <i>Power Supply Recommendations</i> , and <i>Layout</i> sections.....	21



ISO7220A-Q1, ISO7221A-Q1, ISO7221C-Q1
SLLS965E – JULY 2009 – REVISED NOVEMBER 2024

Changes from Revision D (April 2020) to Revision E (November 2024)	Page
• Updated the content throughout the document to better align with the commercial version of the device	1
• Updated reference from capacitive isolation to isolation barrier throughout the document.....	1
• Updated VDE V 0884-11 to DIN VDE 0884-17 throughout the document.....	1
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Updated Thermal Characteristics, Safety Limiting Values, and Thermal Derating Curves to provide more accurate system-level thermal calculations.....	4
• Updated electrical and switching characteristics to match device performance.....	6
• Added the <i>Detailed Description</i> , <i>Overview</i> , <i>Feature Description</i> , <i>Functional Block Diagram</i> , and <i>Device Functional Modes</i> sections.....	16
• Added the <i>Typical Application</i> , <i>Power Supply Recommendations</i> , and <i>Layout</i> sections.....	18



ISO721-Q1, ISO722-Q1
SLLS918D – JULY 2008 – REVISED NOVEMBER 2024

Changes from Revision C (July 2013) to Revision D (November 2024)	Page
• Updated VDE V 0884-11 to DIN VDE 0884-17 throughout the document.....	1
• Updated reference from capacitive isolation to isolation barrier throughout the document.....	1
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Updated Thermal Characteristics, Safety Limiting Values, and Thermal Derating Curves to provide more accurate system-level thermal calculations.....	4
• Updated electrical and switching characteristics to match device performance.....	6
• Added the <i>Detailed Description</i> , <i>Overview</i> , <i>Feature Description</i> , <i>Functional Block Diagram</i> , and <i>Device Functional Modes</i> sections.....	14
• Added the <i>Typical Application</i> , <i>Power Supply Recommendations</i> , and <i>Layout</i> sections.....	16



ISO7231C-Q1
SLLSE71A – SEPTEMBER 2011 – REVISED NOVEMBER 2024

Changes from Revision * (September 2011) to Revision A (November 2024)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Updated reference from capacitive isolation to isolation barrier throughout the document.....	1
• Updated VDE V 0884-11 to DIN VDE 0884-17 throughout the document.....	1
• Updated electrical and switching characteristics to match device performance.....	5
• Changed C ₁ - Typical value from 1 To: 2.....	6
• Changed Figure 4-1 , Figure 4-2 , and Figure 4-3	10
• Added the <i>Detailed Description</i> , <i>Overview</i> , <i>Feature Description</i> , and <i>Device Functional Modes</i> sections.....	14
• Moved the <i>Functional Diagram</i> section to the <i>Detailed Description</i> section and renamed to "Functional Block Diagram" section.....	14
• Added the <i>Typical Application</i> , <i>Design Requirements</i> , <i>Detailed Design Procedure</i> , and <i>Application Curves</i> sections.....	16
• Changed the <i>Life Expectancy vs Working Voltage</i> section to the <i>Insulation Characteristics Curves</i> section and moved under the <i>Application Curves</i> section.....	17
• Added the <i>Documentation Support</i> and <i>Related Documentation</i> sections.....	19

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
ISO724xC-Q1	SLLSE40A	SLLSE40B	http://www.ti.com/product/ISO7240C-Q1

ISO722x-Q1	SLLS965D	SLLS965E	http://www.ti.com/product/ISO7220-Q1
ISO721-Q1, ISO722-Q1	SLLS918C	SLLS918D	http://www.ti.com/product/ISO722-Q1
ISO7231C-Q1	SLLSE71	SLLSE71A	http://www.ti.com/product/ISO7231C-Q1

These changes may be reviewed at the datasheet links provided.

Qual details are provided in the Qual Data Section.

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change

Changes to product identification resulting from this PCN:

Fab Site

Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
RFAB	RFB	USA	Richardson
MIHO8	MH8	JPN	Ibaraki

Die Rev:

Current

New

Die Rev [2P]	Die Rev [2P]
A, B, C, D	-, A

Assembly/Test Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TI Taiwan	TAI	TWN	Chung Ho, New Taipei City
MLA	MLA	MYS	Kuala Lumpur
CD-PR (Probe site)	CDP	CHN	Chengdu

Sample product shipping label (not actual product label):

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7241CQDWRQ1	QBS Process Reference: TCAN1044AEVDRQ1	QBS Package Reference: ISO7240CFQDWRQ1	QBS Package Reference: ISO7241CQDWRQ1	QBS Package Reference: ISO7231CQDWRQ1	QBS Package Reference: ISO7242CQDWRQ1	QBS Package Reference: ISO7241CQDWRQ1
ACU/HAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	1/77/0	-	1/77/0	-	-	-
ACU/HAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	3/231/0	-	-	-	-	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-55C/150C	500 Cycles	3/231/0	-	-	1/77/0	-	-	3/231/0
TC-BP	A4	MIL-STD-883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	-	-	1/5/0	-	-	-
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	-	1/12/0	-	-	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	1/45/0	-	-	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	1000 Hours	-	1/45/0	-	-	-	-	-
Test Group B - Accelerated Lifetime Simulation Tests														
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	1000 Hours	-	3/231/0	-	-	-	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	150C	48 Hours	-	3/2400/0	-	-	-	-	-
Test Group C - Package Assembly Integrity Tests														
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	1/30/0	-	3/90/0	-	-	-
WBP	C2	MIL-STD-883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	1/30/0	-	3/90/0	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	-	-	-	3/30/0	-	-	-
Test Group D - Die Fabrication Reliability Tests														
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDD8	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7241CQDWRQ1	QBS Process Reference: TCAN1044AEVDRQ1	QBS Package Reference: ISO7240CFQDWRQ1	QBS Package Reference: ISO7241CQDWRQ1	QBS Package Reference: ISO7231CQDWRQ1	QBS Package Reference: ISO7242CQDWRQ1	QBS Package Reference: ISO7241CQDWRQ1
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests														
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	12000 Volts	-	1/3/0	-	-	-	-	-
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	-	-	1/3/0	1/3/0	1/3/0	1/3/0	-
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	4000 Volts	-	1/3/0	-	-	-	-	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1500 Volts	-	1/3/0	-	-	-	-	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	-	-	1/3/0	1/3/0	1/3/0	1/3/0	-
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	-	1/6/0	1/3/0	1/3/0	1/3/0	1/3/0	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	-	3/90/0	1/30/0	3/90/0	1/30/0	1/30/0	-
Additional Tests														

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -85C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold: HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room: ACU/HAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2406-026

Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

Q006 {SOIC} at {MLA}
Approve Date 04-November-2024

Attributes	Qual Device: ISO7241CQDWRQ1	QBS Package Reference: ISO7241CQDWRQ1
Automotive Grade Level	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125
Product Function	Interface	Interface
Wafer Fab Supplier	RFAB, MH8, RFAB	RFAB, MH8, RFAB
Assembly Site	MLA	MLA
Package Group	SOIC	SOIC
Package Designator	DW	DW
Pin Count	16	16

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7241CQDWRQ1	QBS Reference: ISO7241CQDWRQ1
Test Group A - Accelerated Environment Stress Tests									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/0/0	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	3/0/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	3/3/0
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	-	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	-	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	-	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	-	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	-	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	3/9/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	-	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	-	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	-	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7241CQDWRQ1	QBS Reference: ISO7241CQDWRQ1
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	3/3/0
TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0	3/9/0
TC	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0	3/9/0
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/231/0	3/231/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0	3/9/0
TC	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0	3/9/0
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	175C	630 Hours	-	-
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	-	3/135/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	175C	1000 Hours	-	-
Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7241CQDWRQ1	QBS Reference: ISO7241CQDWRQ1
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	3/3/0
Test Group C - Package Assembly Integrity Tests									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device ISO7241CQDWRQ1 is qualified at MSL1 260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2406-026

Automotive Qualification Summary
(As per AEC-Q100 Rev. J and JEDEC Guidelines)

ISO RedBull Wave 1 Qual at MLA (8-D Automotive)
Approve Date 04-November-2024

Product Attributes

Attributes	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO722QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Package, Package Reference: ISO6721BQDRQ1	QBS Process Reference: SN74HCS74QPWRQ1	QBS Package Reference: AMC22C12QDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Interface	Interface	Interface	Interface	Logic	Signal Chain
Wafer Fab Supplier	RFAB, RFAB, MH8	RFAB, RFAB, MH8	RFAB, RFAB, MH8	RFAB, RFAB, MH8	RFAB, RFAB, MH8	MH8, MH8	RFAB	MH8, DIMOS6
Assembly Site	MLA	MLA	MLA	MLA	MLA	MLA	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	TSSOP	SOIC
Package Designator	D	D	D	D	D	D	PW	D
Pin Count	8	8	8	8	8	8	14	8

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device ISO721QDRQ1 is qualified at MSL2 260C
- Qual Device ISO7220AQDRQ1 is qualified at MSL2 260C
- Qual Device ISO722QDRQ1 is qualified at MSL2 260C
- Qual Device ISO7221CQDRQ1 is qualified at MSL2 260C
- Qual Device ISO7221AQDRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO722QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Package, Package Reference: ISO6721BQDRQ1	QBS Process Reference: SN74HCS74QPWRQ1	QBS Package Reference: AMC22C12QDRQ1
Test Group A - Accelerated Environment Stress Tests															
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	-	-	-	3/0/0	-	3/0/0	3/0/0	-
Test Group B - Accelerated Lifetime Simulation Tests															
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	-	-	-	-	-	-	3/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	-	-	-	3/231/0	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	-	1/77/0	-	3/231/0	3/231/0	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	-	-	-	-	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	1/77/0	-	-	-	-
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	-	-	1/5/0	-	-	-	-
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	-	-	-	1/12/0	-	1/12/0	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	-	-	3/135/0	-	-
Test Group C - Package Assembly Integrity Tests															
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	-	-	-	-	3/231/0	3/231/0	-
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	408 Hours	-	-	-	-	-	-	-	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	-	-	-	-	3/2400/0	-
Test Group C - Package Assembly Integrity Tests															
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpl0-1.67	Wires	1/30/0	-	-	3/90/0	-	3/228/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpl0-1.67	Wires	1/30/0	-	-	3/90/0	-	3/228/0	3/90/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	-	-	1/15/0	1/15/0	1/15/0
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	-	1/15/0	1/15/0	1/15/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO7221QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Package, Package Reference: ISO6721BQDRQ1	QBS Process Reference: SN74HC874QPWRQ1	QBS Package Reference: AMC22C12QDRQ1
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk=1.67	-	1/10/0	-	-	3/30/0	-	3/30/0	3/30/0	3/30/0
Test Group D - Die Fabrication Reliability Tests															
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDD8	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests															
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk=1.67 Room, hot, and cold	-	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	3/90/0	3/90/0	3/90/0
Additional Tests															

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold: HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room: ACU/HAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2304-011

**Automotive Qualification Summary
(As per AEC and JEDEC Guidelines)**

Q006 {SOIC} at {MLA}
Approve Date 04-November-2024

Attributes	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO722QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Package, Package Reference: ISO6721BQDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Interface	Interface	Interface	Interface
Wafer Fab Supplier	RFAB, RFAB, MH8	RFAB, RFAB, MH8	RFAB, RFAB, MH8	RFAB, RFAB, MH8	RFAB, RFAB, MH8	MH8, MH8
Assembly Site	MLA	MLA	MLA	MLA	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	D	D	D	D	D	D
Pin Count	8	8	8	8	8	8

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO722QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Reference: ISO6721BQDRQ1
Test Group A - Accelerated Environment Stress Tests													
Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO722QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Reference: ISO6721BQDRQ1
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	-	-	-	-	-	3/0/0
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	-	-	-	-	-
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	-	-	-	-	-	-
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	-	-	-	-	-	2/44/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	-	-	-
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-	-	-	-	2/2/0
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	-	-	-	-	-	-
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	-	-	-	-	-	-
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	-	-	-	-	-	-
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	-	-	-	-	-	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	-	-	-	-	-	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	-	-	-	-	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	-	-	-	-	-	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	-	-	-	-	-	3/9/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO722QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Reference: ISO6721BQDRQ1
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	-	-	-	-	-	3/9/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	-	-	-	-	-
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-	-	-	-	-
TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	-	-	-	-	-	-
TC	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	-	-	-	-	-	-
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	-	-	-	-	-	-
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	-	-	-	-	-	3/231/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	-	-	-	-	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	-	-	-	-	3/3/0
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	-	-	-	-	-	3/9/0
TC	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	-	-	-	-	-	3/9/0
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	-	-	-	-	-	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	175C	500 Hours	-	-	-	-	-	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-	-	-	-	-
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	-	-	-	-	-	-

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO721QDRQ1	Qual Device: ISO7220AQDRQ1	Qual Device: ISO722QDRQ1	Qual Device: ISO7221CQDRQ1	Qual Device: ISO7221AQDRQ1	QBS Reference: ISO6721BQDRQ1
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	175C	1000 Hours	-	-	-	-	-	3/135/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	-	-	-	-	3/3/0
Test Group C - Package Assembly Integrity Tests													
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	-	3/90/0	-	3/228/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	-	3/90/0	-	3/228/0

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- Grade 2 (or T): -40C to +105C
- Grade 3 (or J): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/UnHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2304-011

ZVEI ID's: SEM-DE-01, SEM-DE-02, SEM-DE-03, SEM-DS-01, SEM-PW-02, SEM-PW-09, SEM-PW-13, SEM-PA-08, SEM-PA-11, SEM-PA-18, SEM-TF-01

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